

INFORMATION DISCLOSURE CITATION
IN AN APPLICATION

Aug 11 2004 (also several sheets if necessary)

HT-03-025/031

10/849,310

Lopakina *Cheng T. Horwitz et al.*

05/19/04

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U. S. PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

OTHER DOCUMENTS (including Author, Title, Date, Persons, Page(s), Etc.)

PD	-	Y. Ando et al., "Growth mechanisms of thin insulating layer in ferromagnetic tunnel junctions prepared using various oxidation methods," <i>J. Phys. D: Appl. Phys.</i> , Vol. 35, pp. 2415-2421.
PD	-	"Exchange-biased magnetic tunnel junctions and application to nonvolatile magnetic random access memory (invited)", ^b SS.P. Parkin et al., <i>Jrnl. of Applied Physics</i> , Vol. 85, No.8, April 15, 1999, pp. 5828-5833.
EXAMINER	DATE CONSIDERED	
PHUOC T. DANG	3/10/2005	

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.

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<p>Form PTO-1449 INFORMATION DISCLOSURE CITATION IN AN APPLICATION <small>(Use several sheets if necessary)</small> <small>APR 11 2004</small> <small>EXAMINER INITIALS DATE</small> </p>				Document Number (Citation) HT-03-025/031	Application Number 10/849,310			
				Applicant Cheng T. Horng et al.				
				Filing Date 05/19/04	Drawn/Amended			
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FOREIGN PATENT DOCUMENTS								
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OTHER DOCUMENTS (Including Author, Title, Date, Page Numbers, Etc.)								
PD	-	Co-pending U.S. Patent HT-02-032, Ser. # 10/768,917, filed 01/30/04, "A Novel Oxidation Method to Fabricate Low Resistance TMR Read Head", assigned to the same assignee.						
PD	-	Co-pending U.S. Patent HT-03-016, Ser. # 10/820,391, filed 04/08/04, "A Novel Oxidation Structure/Method to Fabricate a High-Performance Magnetic Tunneling Junction Metal", the same " assigned to assignee						
EXAMINER		DATE CONSIDERED						
PHUC T. DANG		3/10/2005						